

**30mA 40V Low VF(0.30mm)**

**Chip Information**

|                   |                  |
|-------------------|------------------|
| Chip Size         | 0.30 x 0.30mm    |
| Pad Size          | 0.13 x 0.13mm    |
| Chip Quantity     | 122959 pcs/wafer |
| Scribe Line Width | 60um             |
| Passivation       | PSG              |
| Wafer Size        | 5 inch           |
| Top Metallization | Al(For Wire)     |

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

| Parameter                               | Symbol  | Limit       | Unit | Note                        |
|---|---------|-------------|------|-----------------------------|
| Repetitive Peak Reverse Voltage         | VRRM    | 40          | V    |                             |
| Non-Repetitive Peak Reverse Voltage     | VRSM    |             | V    |                             |
| Maximum DC Blocking Voltage             | VR      | 40          | V    |                             |
| Average Forward Rectified Current       | IF(AV)  | 30          | mA   |                             |
| Peak Forward Surge Current              | IFSM    | 0.2         | A    | 8.3ms Single Half Sine-Wave |
| Storage and Operating Temperature Range | Tj,TSTG | -65 to +125 | degC |                             |

**ELECTRICAL CHARACTERISTICS**

| Parameter                  | Symbol | Spec Limit | Probe Spec | Typical | Unit | Test Condition       |
|----------------------------|--------|------------|------------|---------|------|----------------------|
| Maximum Forward Voltage    | VF1    | 0.370      | 0.360      | 0.310   | V    | IF=1mA Ta=25degC     |
|                            | VF2    |            |            |         | V    |                      |
|                            | VF3    |            |            |         | V    |                      |
|                            | VF4    |            |            |         | V    |                      |
|                            | VF5    |            |            |         | V    |                      |
| Maximum DC Reverse Current | IR1    | 0.5        | 0.35       | 0.13    | uA   | VR=30V Ta=25degC     |
|                            | IR2    |            |            |         | uA   |                      |
|                            | IR3    |            |            |         | uA   |                      |
|                            | IR4    |            |            |         | uA   |                      |
| Reverse Breakdown Voltage  | BV     | 42         | 45         | 57      | V    | IR=10uA              |
| Junction Capacitance       | Cj     |            |            | 2       | pF   | V=1V,f=1MHz          |
| Reverse Recovery Time      | trr    |            |            | 1       | nS   | IF=IR=10mA irr=0.1IR |

**Ordering Information**

| Chip Type | Chip Thickness | Back Metal       |
|-----------|----------------|------------------|
| YHF035    | 180 +/- 20um   | Au(For Eutectic) |
| YHF037    | 150 +/- 20um   | Au(For Eutectic) |
| YHF039    | 100 +/- 15um   | Au(For Eutectic) |

Note:  
Designed For RB751S-40,RB715F